## ABSOLUTE MAXIMUM RATINGS

These are stress ratings only and functional operation of the device at these ratings or any other above those indicated in the operation sections of the specifications below is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability and cause permanent damage to the device.

$V_{CC}$.....-0.3V to +6.0V
V+ (NOTE 1).....-0.3V to +7.0V
V- (NOTE 1).....+0.3V to -7.0V
V+ + |V-| (NOTE 1).....+13V
$I_{CC}$ (DC $V_{CC}$ or GND current).....±100mA

**Input Voltages**
TxIN, .....-0.3V to +6.0V
RxIN.....±15V
**Output Voltages**
TxOUT.....±13.2V
RxOUT, .....-0.3V to ($V_{CC}$ +0.3V)
**Short-Circuit Duration**
TxOUT.....Continuous

Storage Temperature.....-65°C to +150°C

**Power Dissipation per package**
16-pin SSOP (derate 9.69mW/°C above +70°C).....775mW
16-pin PDIP (derate 14.3mW/°C above +70°C).....1150mW
16-pin Wide SOIC (derate 11.2mW/°C above +70°C).....900mW
16-pin TSSOP (derate 10.5mW/°C above +70°C).....850mW

**NOTE 1**: V+ and V- can have maximum magnitudes of 7V, but their absolute difference cannot exceed 13V.

## ELECTRICAL CHARACTERISTICS

Unless otherwise noted, the following specifications apply for $V_{CC}$ = +3.0V to +5.5V with $T_{AMB}$ = $T_{MIN}$ to $T_{MAX}$

| PARAMETER | MIN. | TYP. | MAX. | UNITS | CONDITIONS |
|---|---|---|---|---|---|
| **DC CHARACTERISTICS** | | | | | |
| Supply Current | | 0.3 | 1.0 | mA | no load, $V_{CC}$ = 3.3V, $T_{AMB}$ = 25°C, TxIN = GND or $V_{CC}$ |
| **LOGIC INPUTS AND RECEIVER OUTPUTS** | | | | | |
| Input Logic Threshold LOW | GND | | 0.8 | V | TxIN |
| Input Logic Threshold HIGH | 2.0 | | Vcc | V | Vcc = 3.3V |
| Input Logic Threshold HIGH | 2.4 | | Vcc | V | Vcc = 5.0V |
| Input Leakage Current | | ±0.01 | ±1.0 | µA | TxIN, $T_{AMB}$ = +25°C |
| Output Voltage LOW | | | 0.4 | V | $I_{OUT}$ = 1.6mA |
| Output Voltage HIGH | $V_{CC}$ -0.6 | $V_{CC}$ -0.1 | | V | $I_{OUT}$ = -1.0mA |
| **DRIVER OUTPUTS** | | | | | |
| Output Voltage Swing | ±5.0 | ±5.4 | | V | All driver outputs loaded with 3kΩ to GND, $T_{AMB}$ = +25°C |

## ELECTRICAL CHARACTERISTICS

Unless otherwise noted, the following specifications apply for $V_{CC}$ = +3.0V to +5.5V with $T_{AMB}$ = $T_{MIN}$ to $T_{MAX}$

| PARAMETER | MIN. | TYP. | MAX. | UNITS | CONDITIONS |
|---|---|---|---|---|---|
| **DRIVER OUTPUTS (continued)** | | | | | |
| Output Resistance | 300 | | | Ω | $V_{CC}$ = V+ = V- = 0V, $V_{OUT}$=±2V |
| Output Short-Circuit Current | | ±35 | ±60 | mA | $V_{OUT}$ = 0V |
| Output Leakage Current | | | ±25 | µA | $V_{CC}$ = 0V, $V_{OUT}$ = ±12V |
| **RECEIVER INPUTS** | | | | | |
| Input Voltage Range | -15 | | 15 | V | |
| Input Threshold LOW | 0.6 | 1.2 | | V | Vcc = 3.3V |
| Input Threshold LOW | 0.8 | 1.5 | | V | Vcc = 5.0V |
| Input Threshold HIGH | | 1.5 | 2.4 | V | Vcc = 3.3V |
| Input Threshold HIGH | | 1.8 | 2.4 | V | Vcc = 5.0V |
| Input Hysteresis | | 0.3 | | V | |
| Input Resistance | 3 | 5 | 7 | kΩ | |
| **TIMING CHARACTERISTICS** | | | | | |
| Maximum Data Rate | 460 | | | kbps | $R_L$ = 3kΩ, $C_L$ = 1000pF, one driver switching |
| Driver Propagation Delay, $t_{PHL}$ | | 1.0 | | µs | $R_L$ = 3kΩ, $C_L$ = 1000pF |
| Driver Propagation Delay, $t_{PLH}$ | | 1.0 | | µs | $R_L$ = 3kΩ, $C_L$ = 1000pF |
| Receiver Propagation Delay, $t_{PHL}$ | | 0.3 | | µs | Receiver input to Receiver output, $C_L$ = 150pF |
| Receiver Propagation Delay, $t_{PLH}$ | | 0.3 | | µs | Receiver input to Receiver output, $C_L$ = 150pF |
| Receiver Output Enable Time | | 200 | | ns | |
| Receiver Output Disable Time | | 200 | | ns | |
| Driver Skew | | 100 | 500 | ns | $\lvert t_{PHL} - t_{PLH} \rvert$ |
| Receiver Skew | | 200 | 1000 | ns | $\lvert t_{PHL} - t_{PLH} \rvert$ |
| Transition-Region Slew Rate | | 60 | | V/µs | Vcc = 3.3V, $R_L$ = 3kΩ, $C_L$ = 1000pF, $T_{AMB}$ = 25°C, measurements taken from -3.0V to +3.0V or +3.0V to -3.0V |

## TYPICAL PERFORMANCE CHARACTERISTICS

Unless otherwise noted, the following performance characteristics apply for $V_{CC}$ = +3.3V, 460kbps data rate, all drivers loaded with 3kΩ, 0.1µF charge pump capacitors, and $T_{AMB}$ = +25°C.

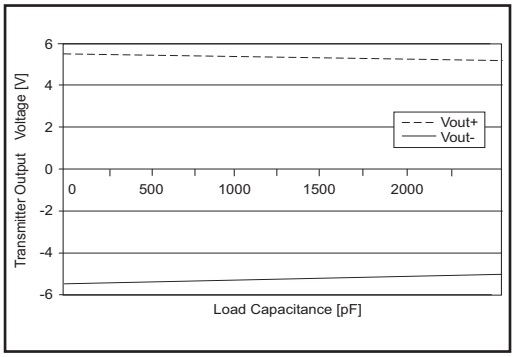



Figure 1. Transmitter Output Voltage vs Load Capacitance

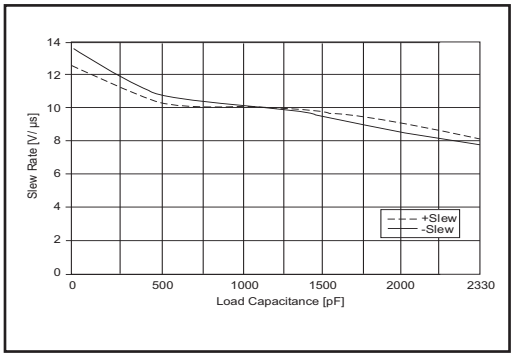



Figure 2. Slew Rate vs Load Capacitance

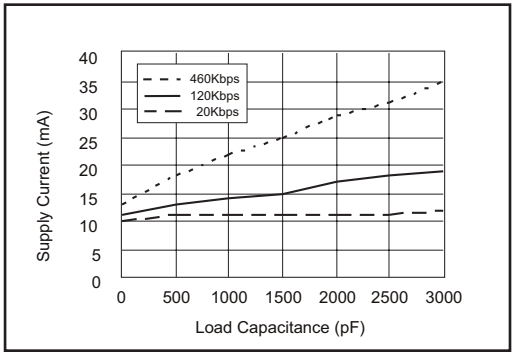



Figure 3. Supply Current VS. Load Capacitance when Transmitting Data

| NAME | FUNCTION | PIN NUMBER |
|---|---|---|
| | | SP3232EH |
| C1+ | Positive terminal of the voltage doubler charge-pump capacitor | 1 |
| V+ | +5.5V output generated by the charge pump | 2 |
| C1- | Negative terminal of the voltage doubler charge-pump capacitor | 3 |
| C2+ | Positive terminal of the inverting charge-pump capacitor | 4 |
| C2- | Negative terminal of the inverting charge-pump capacitor | 5 |
| V- | -5.5V output generated by the charge pump | 6 |
| $T_1OUT$ | RS-232 driver output. | 14 |
| $T_2OUT$ | RS-232 driver output. | 7 |
| $R_1IN$ | RS-232 receiver input | 13 |
| $R_2IN$ | RS-232 receiver input | 8 |
| $R_1OUT$ | TTL/CMOS receiver output | 12 |
| $R_2OUT$ | TTL/CMOS receiver output | 9 |
| $T_1IN$ | TTL/CMOS driver input | 11 |
| $T_2IN$ | TTL/CMOS driver input | 10 |
| GND | Ground. | 15 |
| $V_{CC}$ | +3.0V to +5.5V supply voltage | 16 |

Table 1. Device Pin Description

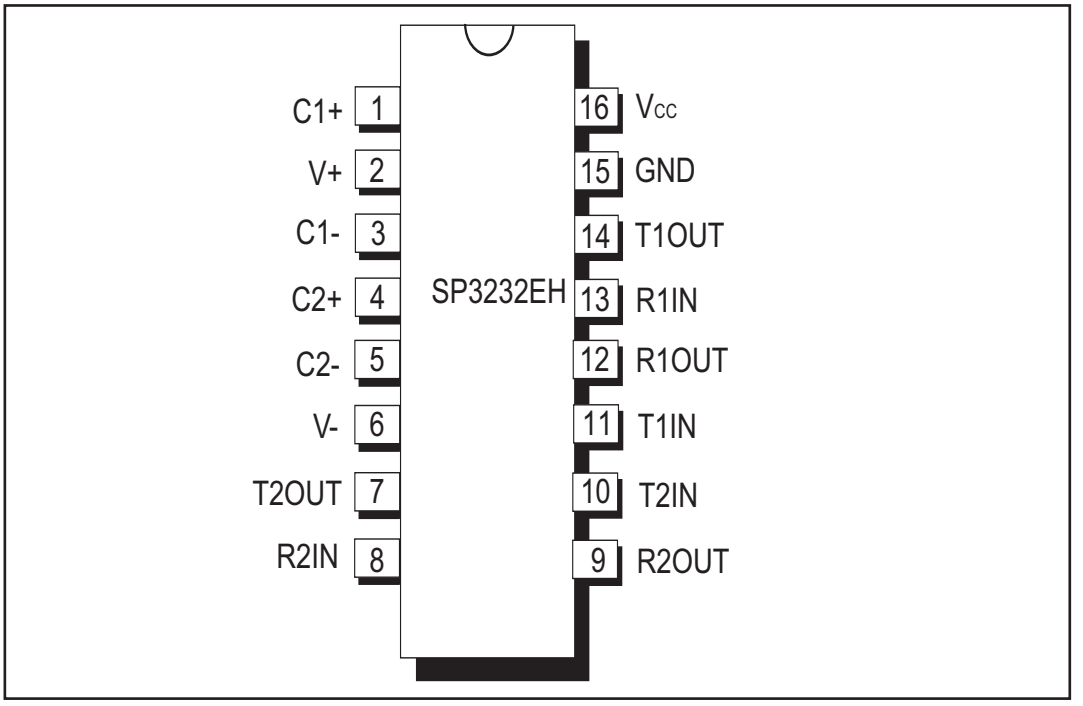



Figure 4. Pinout Configuration for the SP3232EH

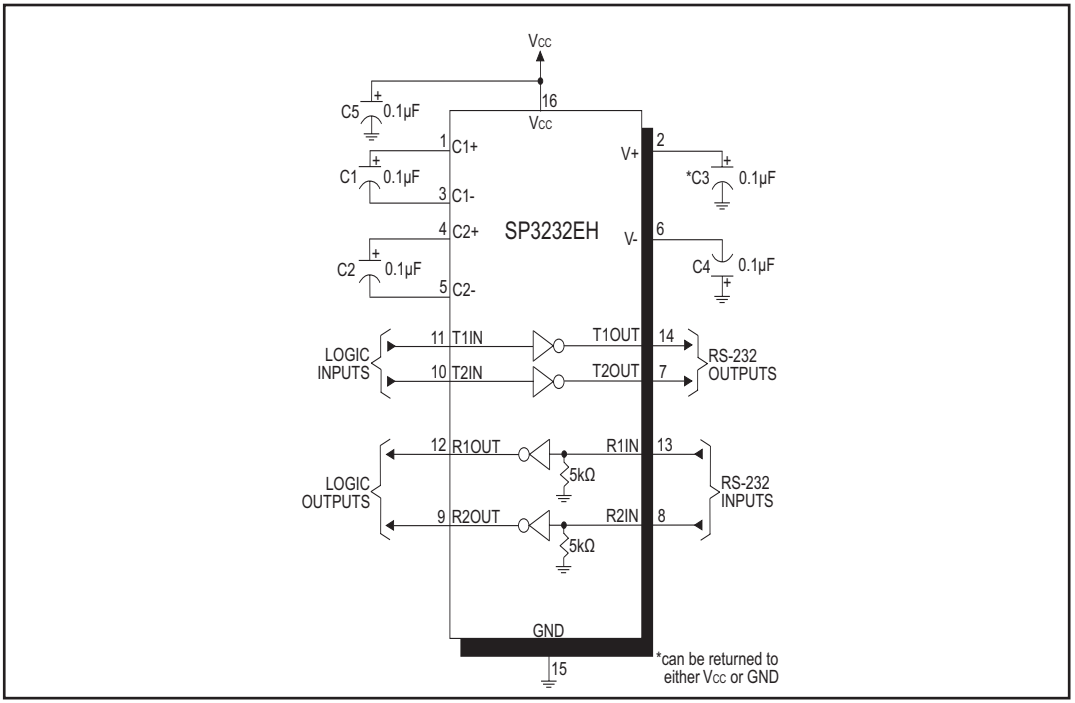



Figure 5. SP3232EH Typical Operating Circuit

The **SP3232EH** is a 2-driver / 2-receiver devices ideal for portable or hand-held applications. The **SP3232EH** transceiver meets the EIA/TIA-232 and ITU-T V.28/V.24 communication protocols and can be implemented in battery-powered, portable, or hand-held applications such as notebook or palmtop computers. The **SP3232EH** device features **Exar's** proprietary on-board charge pump circuitry that generates ±5.5V for RS-232 voltage levels from a single +3.0V to +5.5V power supply. This device is ideal for +3.3V-only systems, mixed +3.3V to +5.5V systems, or +5.0V-only systems that require true RS-232 performance. The **SP3232EH** device can operate at a minimum data rate of 460kbps when fully loaded.

## THEORY OF OPERATION

The **SP3232EH** is made up of three basic circuit blocks:

1. Drivers
2. Receivers
3. The Exar proprietary charge pump

### Drivers

The drivers are inverting level transmitters that convert TTL or CMOS logic levels to ±5.0V EIA/TIA-232 levels with an inverted sense relative to the input logic levels. Typically, the RS-232 output voltage swing is ±5.4V with no load and ±5V minimum fully loaded. The driver outputs are protected against infinite short-circuits to ground without degradation in reliability. Driver outputs will meet EIA/TIA-562 levels of +/-3.7V with supply voltages as low as 2.7V.

The drivers have a minimum data rate of 460kbps fully loaded with 3kΩ in parallel with 1000pF, ensuring compatibility with PC-to-PC communication software.

Figure 6 shows a loopback test circuit used to test the RS-232 Drivers. Figure 7 shows the test results of the loopback circuit with all drivers active at 120kbps with RS-232 loads in parallel with a 1000pF capacitor. Figure 8 shows the test results where one driver was active at 460kbps and all drivers loaded with an RS-232 receiver in parallel with 1000pF capacitor. Designers should connect unused inputs to Vcc or GND.

### Receivers

The Receivers convert EIA/TIA-232 levels to TTL or CMOS logic output levels. Since receiver input is usually from a transmission line where long cable lengths and system interference can degrade the signal, the inputs have a typical hysteresis margin of 300mV. This ensures that the receiver is virtually immune to noisy transmission lines. Should an input be left unconnected, an internal 5kΩ pulldown resistor to ground will commit the output of the receiver to a HIGH state.

### Charge Pump

The charge pump is an Exar-patended design (U.S. 5,306,954) and uses a unique approach compared to older less-efficient designs. The charge pump still requires four external capacitors, but uses a four-phase voltage shifting technique to attain symmetrical 5.5V power supplies. The internal power supply consists of a regulated dual charge pump that provides output voltages of +/-5.5V regardless of the input voltage (Vcc) over the +3.0V to +5.5V range.

In most circumstances, decoupling the power supply can be achieved adequately using a 0.1µF bypass capacitor at C5 (refer to figure 5)

In applications that are sensitive to power-supply noise, decouple Vcc to ground with a capacitor of the same value as charge-pump capacitor C1. Physically connect bypass capacitors as close to the IC as possible.

The charge pump operates in a discontinuous mode using an internal oscillator. If the output voltages are less than a magnitude

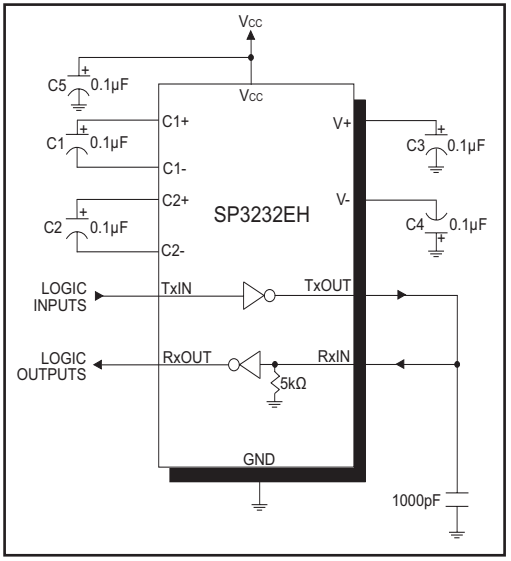



Figure 6. SP3232EH Driver Loopback Test Circuit

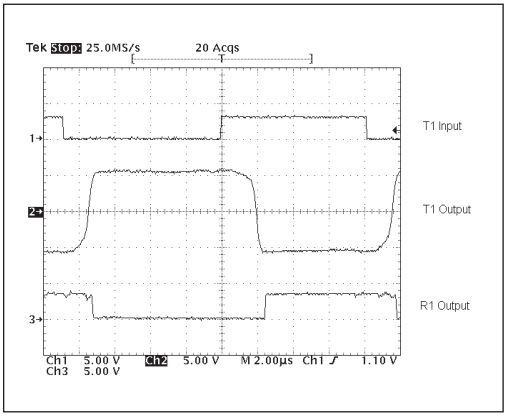



Figure 7. Loopback Test results at 120kbps

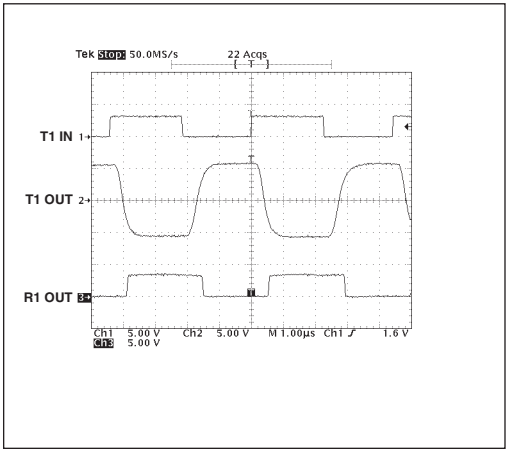



Figure 8. Loopback Test results at 460kbps

of 5.5V, the charge pump is enabled. If the output voltages exceed a magnitude of 5.5V, the charge pump is disabled. This oscillator controls the four phases of the voltage shifting. A description of each phase follows.

**Phase 1**

— $V_{SS}$ charge storage — During this phase of the clock cycle, the positive side of capacitors $C_1$ and $C_2$ are initially charged to $V_{CC}$. $C_1^+$ is then switched to GND and the charge in $C_1^-$ is transferred to $C_2^-$. Since $C_2^+$ is connected to $V_{CC}$, the voltage potential across capacitor $C_2$ is now 2 times $V_{CC}$.

**Phase 2**

— $V_{SS}$ transfer — Phase two of the clock connects the negative terminal of $C_2$ to the $V_{SS}$ storage capacitor and the positive terminal of $C_2$ to GND. This transfers a negative generated voltage to $C_3$. This generated voltage is regulated to a minimum voltage of -5.5V. Simultaneous with the transfer of the voltage to $C_3$, the positive side of capacitor $C_1$ is switched to $V_{CC}$ and the negative side is connected to GND.

**Phase 3**

— $V_{DD}$ charge storage — The third phase of the clock is identical to the first phase — the charge transferred in $C_1$ produces $-V_{CC}$ in the negative terminal of $C_1$, which is applied to the negative side of capacitor $C_2$. Since $C_2^+$ is at $V_{CC}$, the voltage potential across $C_2$ is 2 times $V_{CC}$.

**Phase 4**

— $V_{DD}$ transfer — The fourth phase of the clock connects the negative terminal of $C_2$ to GND, and transfers this positive generated voltage across $C_2$ to $C_4$, the $V_{DD}$ storage capacitor. This voltage is regulated to +5.5V. At this voltage, the internal oscillator is disabled. Simultaneous with the transfer of the voltage to $C_4$, the positive side of capacitor $C_1$ is switched to $V_{CC}$ and the negative side is connected to GND, allowing the charge pump cycle to begin again. The charge pump cycle will continue as long as the operational conditions for the internal oscillator are present.

Since both $V^+$ and $V^-$ are separately generated from $V_{CC}$, in a no–load condition $V^+$ and $V^-$ will be symmetrical. Older charge pump approaches that generate $V^-$ from $V^+$ will show a decrease in the magnitude of $V^-$ compared to $V^+$ due to the inherent inefficiencies in the design.

The clock rate for the charge pump typically operates at greater than 250kHz. The external capacitors can be as low as 0.1µF with a 16V breakdown voltage rating.

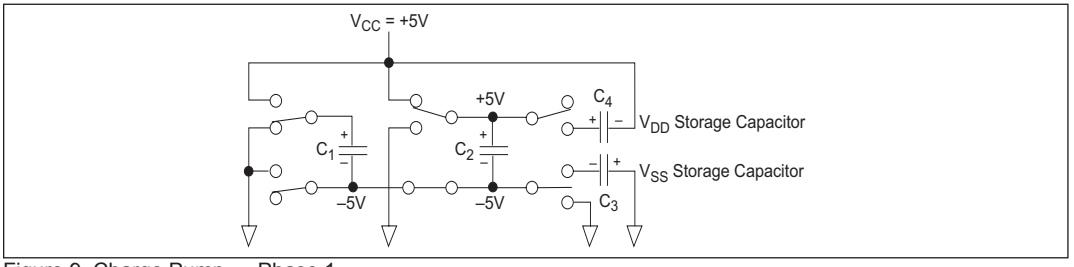



Figure 9. Charge Pump — Phase 1

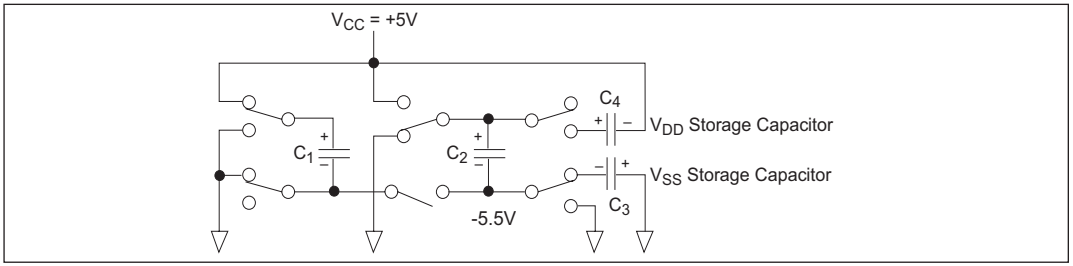



Figure 10. Charge Pump — Phase 2

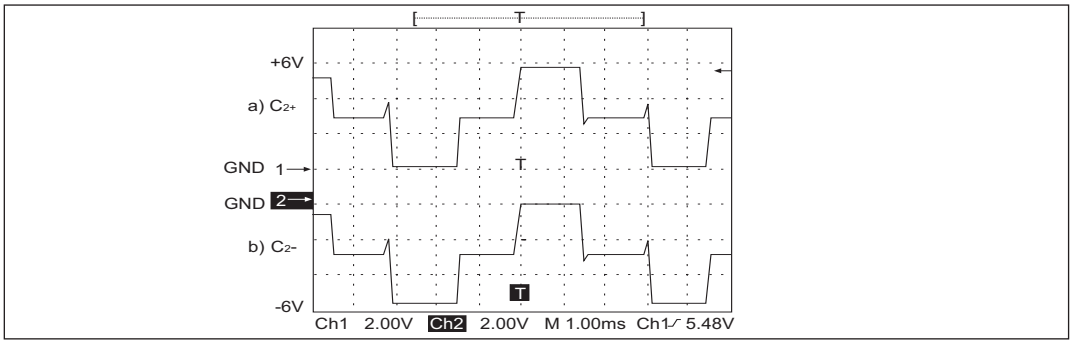



Figure 11. Charge Pump Waveforms

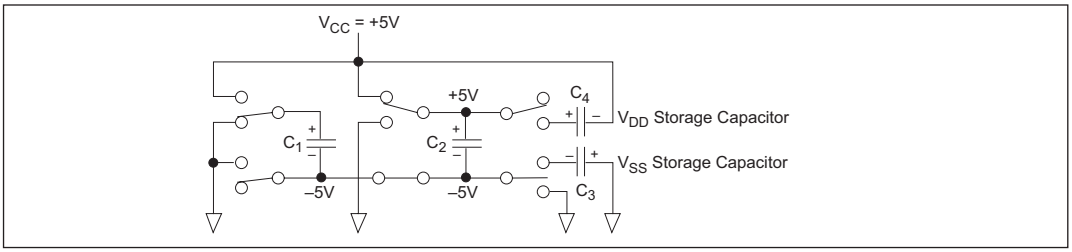



Figure 12. Charge Pump — Phase 3

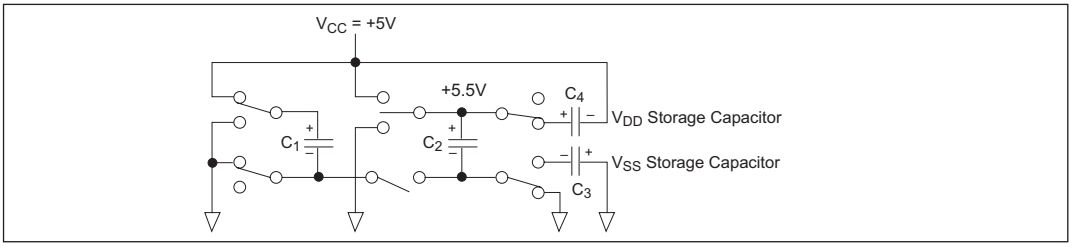



Figure 13. Charge Pump — Phase 4

## ESD TOLERANCE

The **SP3232EH** device incorporates ruggedized ESD cells on all driver output and receiver input pins. The ESD structure is improved over our previous family for more rugged applications and environments sensitive to electro-static discharges and associated transients. The improved ESD tolerance is at least ±15kV without damage nor latch-up.

There are different methods of ESD testing applied:

a) MIL-STD-883, Method 3015.7
b) IEC61000-4-2 Air-Discharge
c) IEC61000-4-2 Direct Contact

The Human Body Model has been the generally accepted ESD testing method for semi-conductors. This method is also specified in MIL-STD-883, Method 3015.7 for ESD testing. The premise of this ESD test is to simulate the human body's potential to store electro-static energy and discharge it to an integrated circuit. The simulation is performed by using a test model as shown in Figure 14. This method will test the IC's capability to withstand an ESD transient during normal handling such as in manufacturing areas where the IC's tend to be handled frequently.

The IEC-61000-4-2, formerly IEC801-2, is generally used for testing ESD on equipment and systems. For system manufacturers, they must guarantee a certain amount of ESD protection since the system itself is exposed to the outside environment and human presence. The premise with IEC61000-4-2 is that the system is required to withstand an amount of static electricity when ESD is applied to points and surfaces of the equipment that are accessible to personnel during normal usage. The transceiver IC receives most of the ESD current when the ESD source is applied to the connector pins. The test circuit for IEC61000-4-2 is shown on Figure 15. There are two methods within IEC61000-4-2, the Air Discharge method and the Contact Discharge method.

With the Air Discharge Method, an ESD voltage is applied to the equipment under test (EUT) through air. This simulates an electrically charged person ready to connect a cable onto the rear of the system only to find an unpleasant zap just before the person touches the back panel. The high energy potential on the person discharges through an arcing path to the rear panel of the system before he or she even touches the system. This energy, whether discharged directly or through air, is predominantly a function of the discharge current rather than the discharge voltage. Variables with an air discharge such as approach speed of the object carrying the ESD potential to the system and humidity will tend to change the discharge current. For example, the rise time of the discharge current varies with the approach speed.

The Contact Discharge Method applies the ESD current directly to the EUT. This method was devised to reduce the unpredictability of the ESD arc. The discharge current rise time is constant since the energy is directly transferred without the air-gap arc. In situations such as hand held systems, the ESD charge can be directly discharged to the

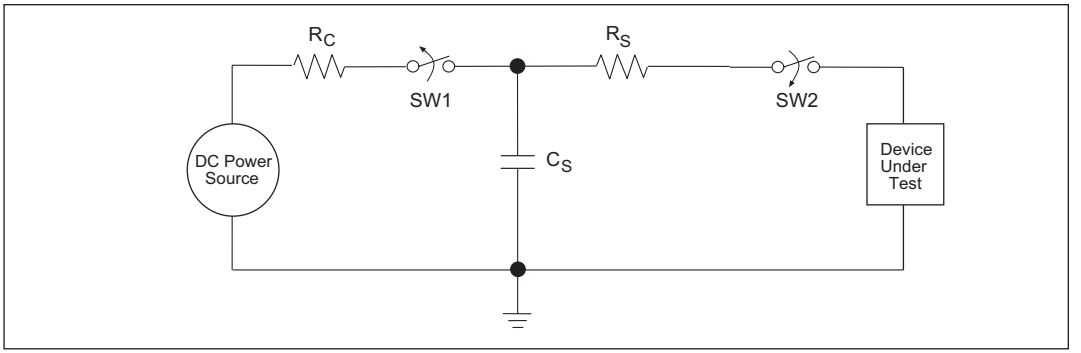



Figure 14. ESD Test Circuit for Human Body Model

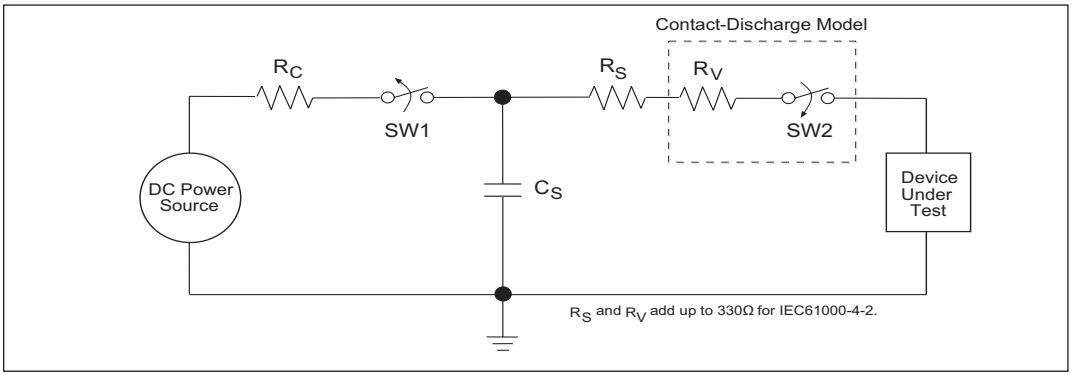



Figure 15. ESD Test Circuit for IEC61000-4-2

equipment from a person already holding the equipment. The current is transferred on to the keypad or the serial port of the equipment directly and then travels through the PCB and finally to the IC.

The circuit models in Figures 14 and 15 represent the typical ESD testing circuit used for all three methods. The $C_S$ is initially charged with the DC power supply when the first switch (SW1) is on. Now that the capacitor is charged, the second switch (SW2) is on while SW1 switches off. The voltage stored in the capacitor is then applied through $R_S$, the current limiting resistor, onto the device under test (DUT). In ESD tests, the SW2 switch is pulsed so that the device under test receives a duration of voltage.

For the Human Body Model, the current limiting resistor ($R_S$) and the source capacitor ($C_S$) are 1.5kΩ an 100pF, respectively. For IEC-61000-4-2, the current limiting resistor ($R_S$) and the source capacitor ($C_S$) are 330Ω an 150pF, respectively.

The higher $C_S$ value and lower $R_S$ value in the IEC61000-4-2 model are more stringent than the Human Body Model. The larger storage capacitor injects a higher voltage to the test point when SW2 is switched on. The lower current limiting resistor increases the current charge onto the test point.

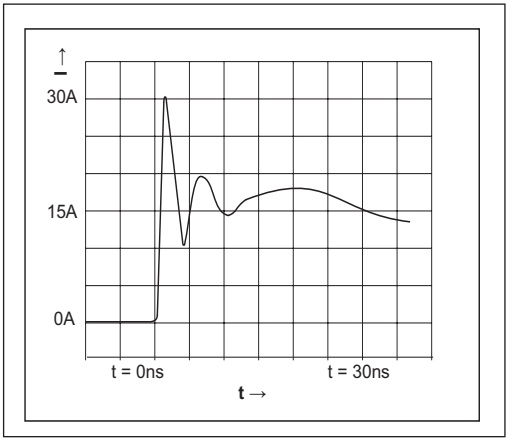
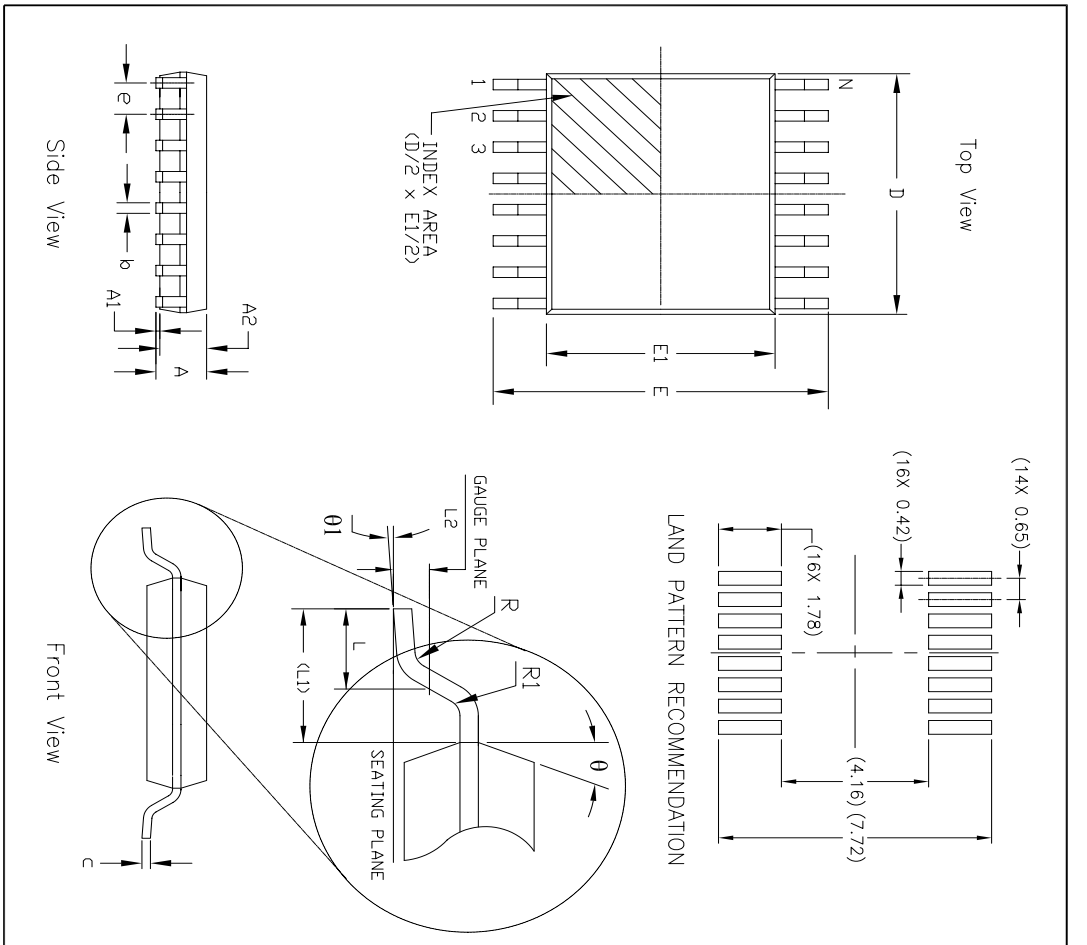



Figure 16. ESD Test Waveform for IEC61000-4-2

| DEVICE PIN TESTED | HUMAN BODY MODEL | IEC61000-4-2 | | |
|---|---|---|---|---|
| | | Air Discharge | Direct Contact | Level |
| Driver Outputs | ±15kV | ±15kV | ±8kV | 4 |
| Receiver Inputs | ±15kV | ±15kV | ±8kV | 4 |

Table 2. Transceiver ESD Tolerance Levels




REVISION HISTORY

| REV. | DISCRIPTION | DATE | APP'D |
|---|---|---|---|
| A | DRAWING ORIGINATION | 04/19/06 | JL |
| B | ADD LAND PATTERN RECOMMENDATION | 05/22/07 | JL |
| C | CHANGE DRAWING LOGO AND COMPANY NAME | 11/21/07 | JL |

16 Pin TSSOP JEDEC MO-153 Variation AB

| SYMBOLS | DIMENSIONS IN MM (Control Unit) | | | DIMENSIONS IN INCH (Reference Unit) | | |
|---|---|---|---|---|---|---|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | — | — | 1.20 | — | — | 0.047 |
| A1 | 0.05 | — | 0.15 | 0.002 | — | 0.006 |
| A2 | 0.80 | 1.00 | 1.05 | 0.031 | 0.039 | 0.041 |
| b | 0.19 | — | 0.30 | 0.007 | — | 0.012 |
| c | 0.09 | — | 0.20 | 0.004 | — | 0.008 |
| E | 6.40 BSC | | | 0.252 BSC | | |
| E1 | 4.30 | 4.40 | 4.50 | 0.169 | 0.173 | 0.177 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.45 | 0.60 | 0.75 | 0.018 | 0.024 | 0.030 |
| L1 | 1.00 REF | | | 0.039 REF | | |
| L2 | 0.25 BSC | | | 0.010 BSC | | |
| R | 0.09 | — | — | 0.035 | — | — |
| R1 | 0.09 | — | — | 0.035 | — | — |
| θ | 12° REF | | | 12° REF | | |
| θ1 | 0° | — | 8° | 0° | — | 8° |
| D | 4.90 | 5.00 | 5.10 | 0.193 | 0.197 | 0.200 |
| N | 16 | | | 16 | | |

EXAR CORPORATION

16 PIN TSSOP PACKAGE OUTLINE

| Packaging Approval: | Drawing No: | 16-PIN TSSOP |
|---|---|---|
| By: JL | Revision: C | Sheet: 1 OF 1 |
| Date: 11/21/07 | | |

| Part Number | Temp. Range | Package |
|---|---|---|
| SP3232EHCY-L | 0°C to +70°C | 16 Pin TSSOP |
| SP3232EHCY-L/TR | 0°C to +70°C | 16 Pin TSSOP |
| SP3232EHEY-L | -40°C to +85°C | 16 Pin TSSOP |
| SP3232EHEY-L/TR | -40°C to +85°C | 16 Pin TSSOP |

Note: "/TR" is for tape and Reel option. "-L" is for lead free packaging

# REVISION HISTORY

| DATE | REVISION | DESCRIPTION |
|---|---|---|
| 01/18/06 | -- | Legacy Sipex Datasheet |
| 01/06/11 | 1.0.0 | Convert to Exar Format, Remove EOL device SP3222EH, update ordering information and change revision to 1.0.0. |
| 06/07/11 | 1.0.1 | Remove obsolete devices per PDN 110510-01. |
| 03/14/13 | 1.0.2 | Correct type error to RX input voltage ABS Maximum Rating and TX transition region slew rate condition. |



Datasheet March 2013

For technical questions please email Exar's Serial Technical Support group at: serialtechsupport@exar.com